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MEMORY CELL, MEMORY CIRCUIT BLOCK, DATAWRITING METHOD AND DATA READING METHOD

ABSTRACT

An object of the present invention is to provide a memory cell, a memory circuit block, a data writing method, and a data reading method which realize a reduction in the number of metal layers, cost, and the chip size and an increase of production yields and product reliability. A memory cell (12) comprises a metal line (16) crossing a bit line (14) without contact therewith and a second conductive structure (24) connecting the metal line (16) and a switching element (20). A write driver circuit (26) for driving a write current through the metal line (16) and a ground (28) are connected to the metal line (16) through a switch (30) for selecting the circuit (26) or the ground (28).

FIG. 1